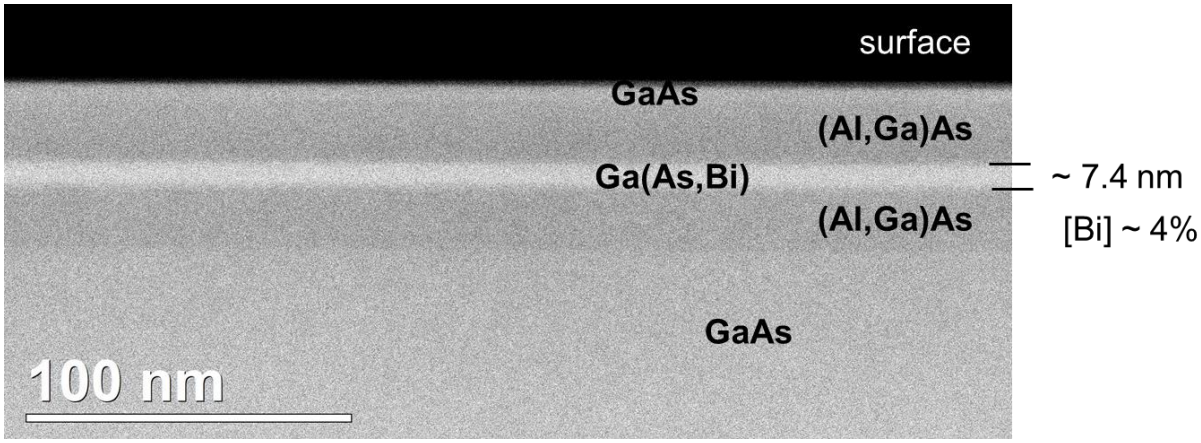

Fig. 1. High-angle annular dark-field (HAADF) image with atomic number Z-contrast of the 7 nm thick Ga(As,Bi) QW with 20 nm thick (Al,Ga)As barriers. The expected HAADF bright contrast of the QW is due to the presence of Bi, $Z_{Bi} = 83$, in the layer.

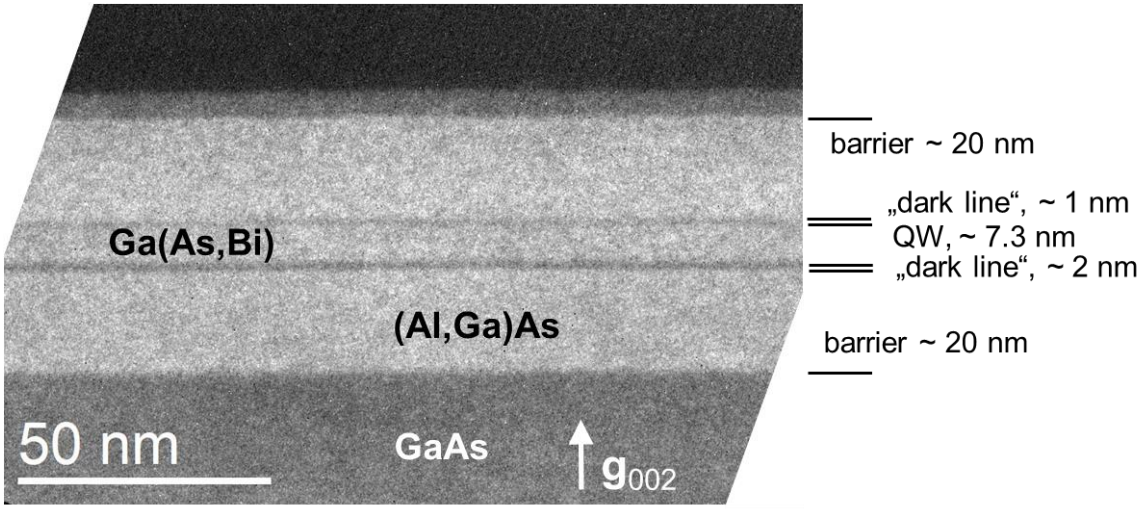

Fig. 2. Chemically-sensitive $\mathbf{g}_{002}$ dark-field TEM micrograph of the Ga(As,Bi) QW with 20 nm thick (Al,Ga)As barriers. Note the presence of two lines with darker contrast delimiting the interface position, at the location of the growth interruptions (GI).

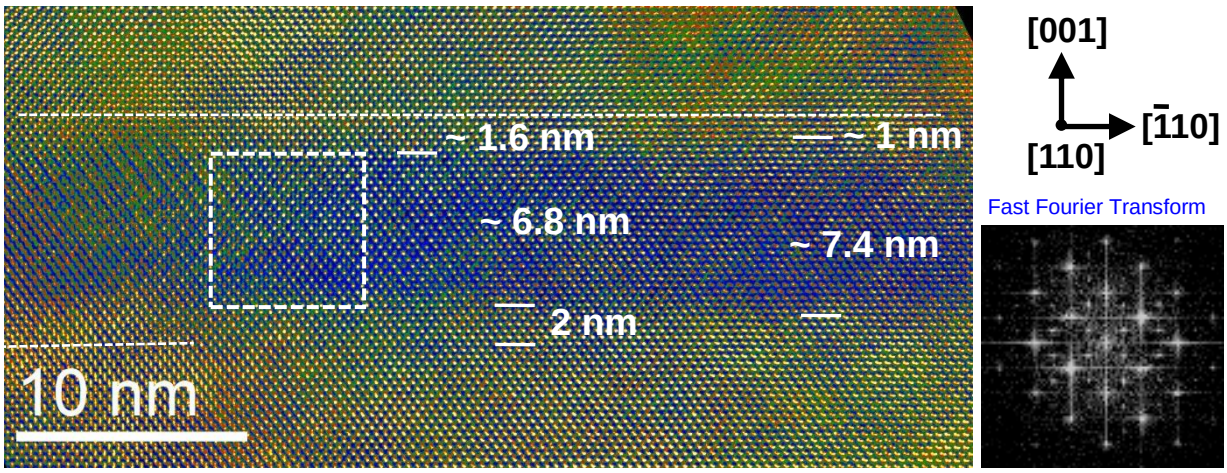

Fig. 3. High-resolution (HR) TEM micrograph of the Ga(As,Bi) QW. $CuPt_B$ atomic ordering is detected inside the 7-nm-thick QW but not at two unintentional layers before and after the QW, at the GI positions.